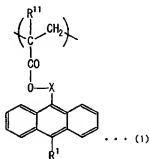
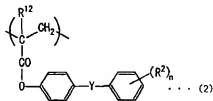


ABSTRACT OF THE DISCLOSURE

There is provided a base material for lithography that is capable of achieving superior film formation characteristics, while maintaining good light absorption characteristics. The base material for lithography comprises (a) a cross linking agent formed from a specific nitrogen containing compound, (b) a copolymer comprising two types of (meth)acrylate ester units as represented by the general formulas (1) and (2) shown below, and (c) an organic solvent:



wherein, R^1 represents a hydroxyl group or a carboxyl group or the like, and X represents an alkyl chain of 1 to 4 carbon atoms; and



wherein, R^2 represents a hydroxyl group or a carboxyl group or the like, Y represents - SO_2 -, -CO- or -SO-; and n represents a number from 1 to 4.